

**ABSTRACT OF THE DISCLOSURE**

When a phase shift method is used as lithography where sense  
amplifiers are alternately placed in a one intersecting-point  
5 memory capable of implementing a reduction in the area of a DRAM,  
it was difficult to layout data lines in a boundary region between  
sense amplifiers and each memory array. Therefore, there is  
provided a semiconductor device according to the present  
invention. In the semiconductor device, two data lines  
10 continuous within the sub memory arrays or interposed  
therebetween are connected to the adjacent sense amplifiers as  
a system for drawing data lines from sub memory arrays (SMA) to  
sense amplifiers (SA) when the sense amplifiers are alternately  
placed. Namely, the number of data lines interposed between data  
15 lines respectively connected to two adjacent sense amplifiers  
is set to even numbers (0, 2, 4, ...). Owing to the above  
configuration, a break and a short circuit in a portion where  
a sense amplifier block and a sub memory array are connected,  
can be avoided, and a connection layout is facilitated.